

- Operates from 1.65 V to 3.6 V
- Max t_{pd} of 2.8 ns at 3.3 V
- ±24-mA Output Drive at 3.3 V
- Latch-up Performance Exceeds 250 mA Per JESD 17
- ESD Performance Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

DESCRIPTION/ORDERING INFORMATION

This quadruple bus buffer gate is designed for 1.65-V to 3.6-V V_{CC} operation.

The SN74ALVC125 features independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (\overline{OE}) input is high.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

the minimum	value of the resisto	or is determined by t	he current-sinking capability	of the driver.
		ORDERING INFO	RMATION	
T _A	PACK	AGE ⁽¹⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	SOIC - D	Tube	SN74ALVC125D	ALVC125

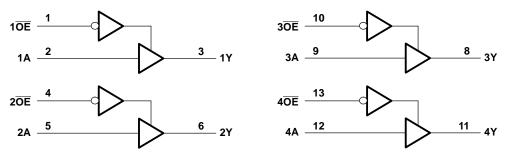
	SOIC - D	Tube	SN74ALVC125D	ALVC125	
	3010 - D	Tape and reel	SN74ALVC125DR	ALVC125	
-40°C to 85°C	SOP - NS	Tape and reel	SN74ALVC125NSR	ALVC125	
-40 C 10 85 C	TSSOP - PW	Tube	SN74ALVC125PW	VA125	
	1330F - FW	Tape and reel	SN74ALVC125PWR	VAIZS	
	TVSOP - DGV	Tape and reel	SN74ALVC125DGVR	VA125	

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTION TABLE (each buffer)

INPU	JTS	OUTPUT
OE	Α	Y
L	Н	н
L	L	L
н	Х	Z

LOGIC DIAGRAM (POSITIVE LOGIC)



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters. SCES110H-JULY 1997-REVISED SEPTEMBER 2004

A

D, DGV, NS, OR PW PACKAGE (TOP VIEW) 1OE 14 V_{CC} 13 🛛 40E 1A Γ 2 12 🛛 4A 1Y 3 $2\overline{OE}$ 11 **1** 4Y 4 2A 5 10 3<u>0</u>E Ш 2Y 9 🛛 3A 6

8 3Y

GND

7

SN74ALVC125 QUADRUPLE BUS BUFFER GATE WITH 3-STATE OUTPUTS

SCES110H-JULY 1997-REVISED SEPTEMBER 2004



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		-0.5	4.6	V
VI	Input voltage range ⁽²⁾		-0.5	4.6	V
Vo	Output voltage range ⁽²⁾⁽³⁾		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V ₁ < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
I _O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
		D package		86	
0	Deckers thermal impedance (4)	DGV package		127	°C/W
θ_{JA}	Package thermal impedance ⁽⁴⁾	NS package		76	-C/W
		PW package		113	
T _{stg}	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

(3) This value is limited to 4.6 V maximum.

(2)

(4) The package thermal impedance is calculated in accordance with JESD 51-7.

RECOMMENDED OPERATING CONDITIONS⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		1.65	3.6	V
		V _{CC} = 1.65 V to 1.95 V	$0.65 imes V_{CC}$		
VIH	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	2		
		V_{CC} = 1.65 V to 1.95 V		$0.35 \times V_{CC}$	
V _{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
VI	Input voltage		0	3.6	V
Vo	Output voltage		0	V _{CC}	V
		V _{CC} = 1.65 V		-4	
	Lich lovel output ourrest	$V_{CC} = 2.3 V$		-12	mA
I _{OH}	High-level output current	$V_{CC} = 2.7 V$		-12	mA
		$V_{CC} = 3 V$		-24	
		V _{CC} = 1.65 V		4	
	L Low-level output current	$V_{CC} = 2.3 V$		12	~ ^
I _{OL}		$V_{CC} = 2.7 V$		12	mA
		$V_{CC} = 3 V$		24	
T _A	Operating free-air temperature		-40	85	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



SN74ALVC125 QUADRUPLE BUS BUFFER GATE WITH 3-STATE OUTPUTS

SCES110H-JULY 1997-REVISED SEPTEMBER 2004

ELECTRICAL CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{cc}	MIN TYP ⁽¹⁾	MAX	UNIT	
	I _{OH} = -100 μA	1.65 V to 3.6 V	V _{CC} - 0.2			
	I _{OH} = -4 mA	1.65 V	1.2			
	I _{OH} = -6 mA	2.3 V	2			
V _{OH}		2.3 V	1.7		V	
	I _{OH} = -12 mA	2.7 V	2.2			
		3 V	2.4			
	I _{OH} = -24 mA	3 V	2			
	I _{OL} = 100 μA	1.65 V to 3.6 V		0.2		
	$I_{OL} = 4 \text{ mA}$	1.65 V		0.45	V	
M	$I_{OL} = 6 \text{ mA}$	2.3 V		0.4		
V _{OL}	L = 12 mA	2.3 V		0.7		
	$I_{OL} = 12 \text{ mA}$	2.7 V		0.4		
	$I_{OL} = 24 \text{ mA}$	3 V		0.55		
l _l	$V_{I} = V_{CC}$ or GND	3.6 V		±5	μA	
I _{OZ}	$V_{O} = V_{CC} \text{ or } GND$	3.6 V		±10	μA	
I _{CC}	$V_{I} = V_{CC} \text{ or } GND, \qquad I_{O} = 0$	3.6 V		10	μA	
ΔI_{CC}	One input at V _{CC} - 0.6 V, Other inputs at V _{CC} or GND	3 V to 3.6 V		750	μA	
Control inpu	$\frac{1}{1}$	221/	3.5		۶Ē	
C _i Data inputs	$V_{I} = V_{CC} \text{ or } GND$	3.3 V	3.5	pF		
C _o Outputs	$V_0 = V_{CC}$ or GND	3.3 V	5.5		pF	

(1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

PARAMETER FROM (INPUT)		TO (OUTPUT)	V _{CC} = ± 0.1	1.8 V 5 V	V _{CC} = 1 ± 0.2	2.5 V 2 V	V _{CC} =	2.7 V	V _{CC} = 3 ± 0.3	3.3 V 3 V	UNIT
	(INPOT)	(001201)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	А	Y	1.3	5.3	1	3.2		3.1	1.1	2.8	ns
t _{en}	OE	Y	1.4	6.4	1	4.1		4.3	1	3.5	ns
t _{dis}	OE	Y	1.8	5.9	1	3.4		4	1.4	4	ns

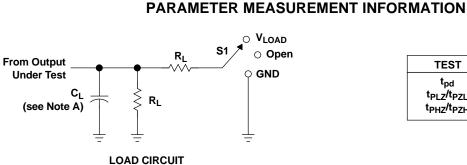
OPERATING CHARACTERISTICS

 $T_A = 25^{\circ}C$

A								
	PARAMETER		TEST	V _{CC} = 1.8 V	$V_{CC} = 2.5 V$	V _{CC} = 3.3 V	UNIT	
	FARAMETER		CONDITIONS	ТҮР	TYP	TYP	UNIT	
C	Power dissipation	Outputs enabled	$C_{L} = 0,$	15	17	19	ρF	
C _{pd}	capacitance per gate	Outputs disabled	f = 10 MHz	2	2	3	pr	

SN74ALVC125 QUADRUPLE BUS BUFFER GATE WITH 3-STATE OUTPUTS



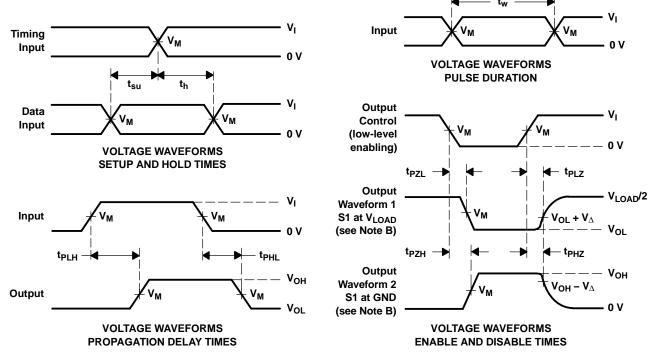


TEST	S1
t _{pd}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

IEXAS RUMENTS

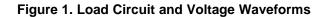
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ſ	V	INPUT		V	v	6	Р	v
	V _{CC}	VI	t _r /t _f	V _M	V _{LOAD}	C∟	RL	V_{Δ}
ſ	1.8 V \pm 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
	2.5 V \pm 0.2 V	V _{CC}	≤2 ns	V _{CC} /2	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
	2.7 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
	3.3 V \pm 0.3 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.





10-Jun-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
SN74ALVC125D	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	ALVC125	Samples
SN74ALVC125DE4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	ALVC125	Samples
SN74ALVC125DG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	ALVC125	Samples
SN74ALVC125DGVR	ACTIVE	TVSOP	DGV	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VA125	Samples
SN74ALVC125DR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	ALVC125	Samples
SN74ALVC125DRE4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	ALVC125	Samples
SN74ALVC125DRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	ALVC125	Samples
SN74ALVC125NSR	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	ALVC125	Samples
SN74ALVC125NSRE4	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	ALVC125	Samples
SN74ALVC125PW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VA125	Samples
SN74ALVC125PWE4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VA125	Samples
SN74ALVC125PWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VA125	Samples
SN74ALVC125PWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VA125	Samples
SN74ALVC125PWRE4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VA125	Samples
SN74ALVC125PWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VA125	Samples

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.



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10-Jun-2014

PREVIEW: Device has been announced but is not in production. Samples may or may not be available. **OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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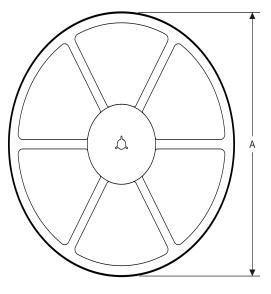
PACKAGE MATERIALS INFORMATION

TEXAS INSTRUMENTS

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TAPE AND REEL INFORMATION

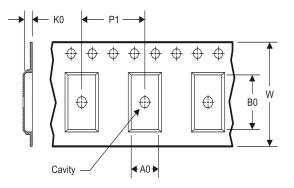
REEL DIMENSIONS





TAPE AND REEL INFORMATION

TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74ALVC125DGVR	TVSOP	DGV	14	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74ALVC125DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74ALVC125NSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN74ALVC125PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

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PACKAGE MATERIALS INFORMATION

14-Jul-2012



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74ALVC125DGVR	TVSOP	DGV	14	2000	367.0	367.0	35.0
SN74ALVC125DR	SOIC	D	14	2500	367.0	367.0	38.0
SN74ALVC125NSR	SO	NS	14	2000	367.0	367.0	38.0
SN74ALVC125PWR	TSSOP	PW	14	2000	367.0	367.0	35.0

MECHANICAL DATA

PLASTIC SMALL-OUTLINE PACKAGE

0,51 0,35 ⊕0,25⊛ 1,27 8 14 0,15 NOM 5,60 8,20 5,00 7,40 \bigcirc Gage Plane ₽ 0,25 7 1 1,05 0,55 0-10 Δ 0,15 0,05 Seating Plane - 2,00 MAX 0,10PINS ** 14 16 20 24 DIM 10,50 10,50 12,90 15,30 A MAX A MIN 9,90 9,90 12,30 14,70 4040062/C 03/03

NOTES: A. All linear dimensions are in millimeters.

NS (R-PDSO-G**)

14-PINS SHOWN

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



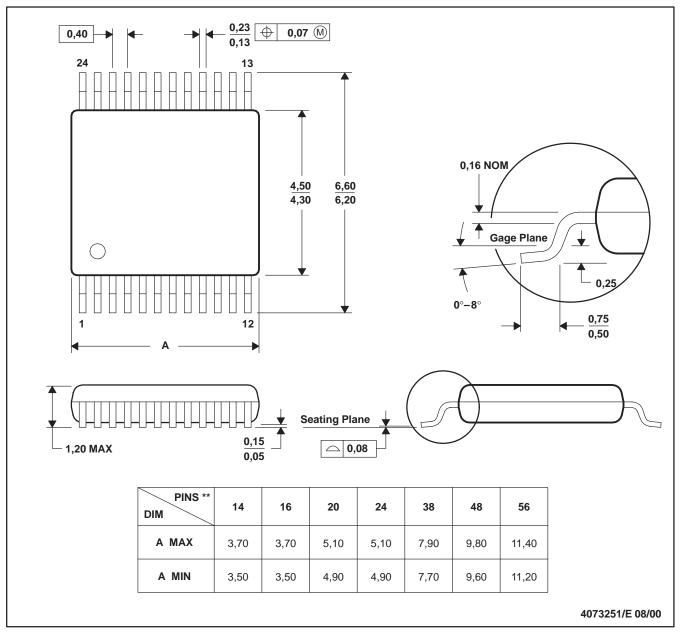
MECHANICAL DATA

PLASTIC SMALL-OUTLINE

MPDS006C - FEBRUARY 1996 - REVISED AUGUST 2000

DGV (R-PDSO-G**)

24 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

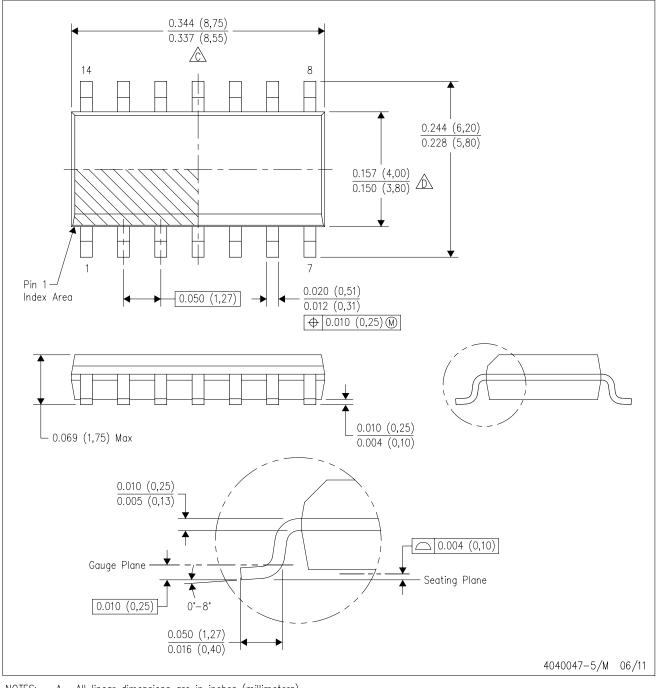
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
- D. Falls within JEDEC: 24/48 Pins MO-153

14/16/20/56 Pins – MO-194



D (R-PDSO-G14)

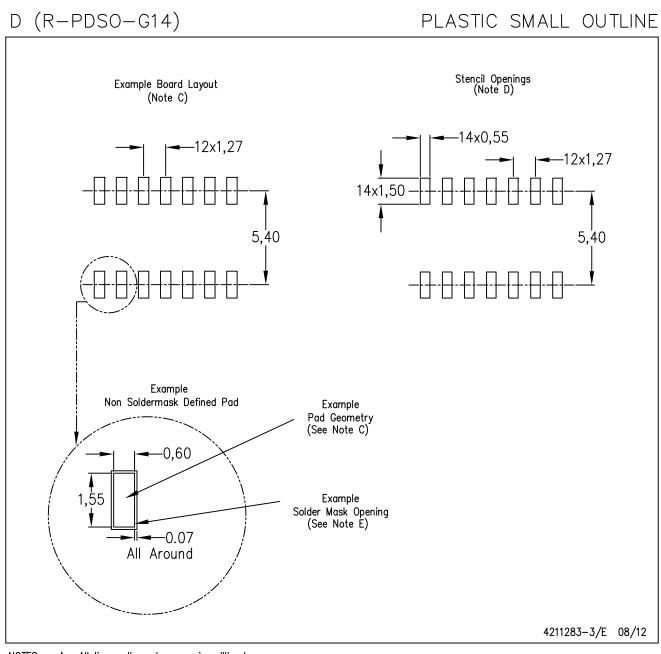
PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.





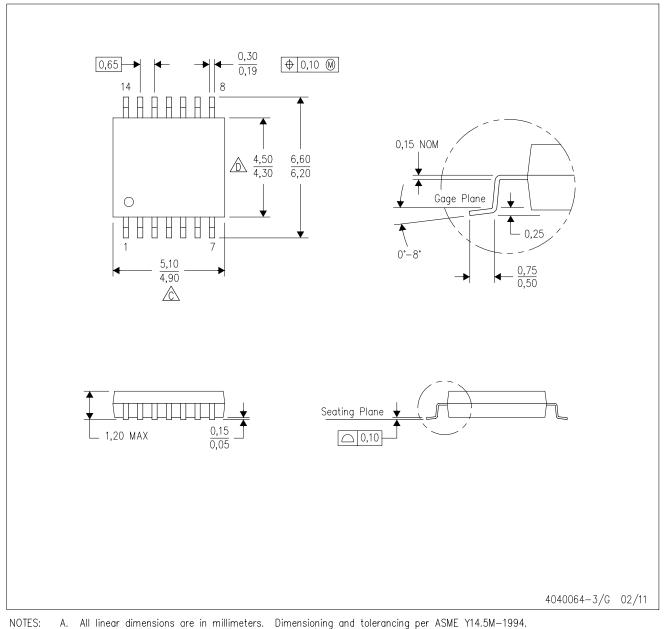
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



B. This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.

Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.

E. Falls within JEDEC MO-153



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